Product data sheet

1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

2. Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

3. Applications

- 12 V, 24 V and 42 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	-	39	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	-	158	W
Static charac	cteristics					
R _{DSon}	drain-source on-state	V_{GS} = 4.5 V; I_D = 25 A; T_j = 25 °C	-	-	43	mΩ
	resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	29	39	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; Fig. 11; Fig. 12	-	34	40	mΩ
Dynamic cha	racteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; V_{DS} = 80 \text{ V};$ $T_j = 25 \text{ °C}; Fig. 13$	-	20	-	nC



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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Avalanche ruggedness							
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 39 A; $V_{sup} \le$ 100 V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	182	mJ

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D 1
2	D	drain[1]		
3	S	source		G T T
mb	D	mounting base; connected to drain	D2PAK (SOT404)	mbb076 S

^[1] It is not possible to make a connection to pin 2.

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BUK9640-100A	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404			

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9640-100A	BUK9640-100A

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 k Ω	-	100	V
V_{GS}	gate-source voltage		-15	15	V

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Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	158	W
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 5 V; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	39	Α
		T _{mb} = 100 °C; V _{GS} = 5 V; <u>Fig. 2</u>	-	28	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 3	-	159	Α
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	n diode				
I _S	source current	T _{mb} = 25 °C	-	39	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	159	Α
Avalanche r	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 39 A; $V_{sup} \le 100$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped	-	182	mJ

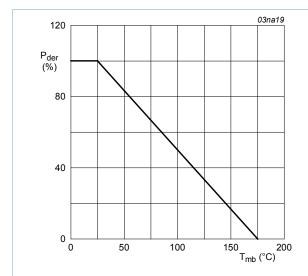


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

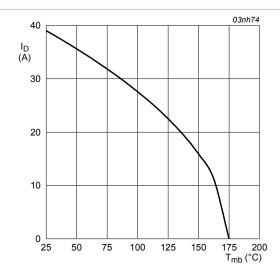


Fig. 2. Normalized continuous drain current as a function of mounting base temperature

$$T_{amb} = 25^{\circ}C; I_{DM}$$
 is single pulse

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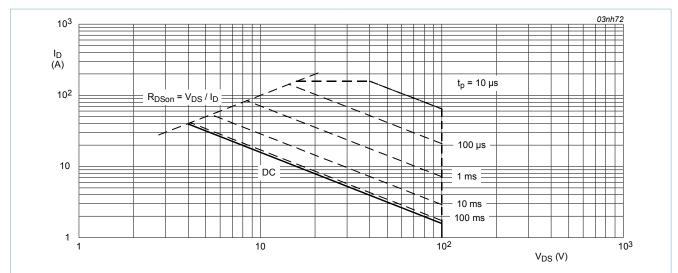


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$$T_{amb} = 25^{\circ}C; I_{DM}$$
 is single pulse

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4	-	-	0.95	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	mounted on a printed-circuit board; minimum footprint	-	50	-	K/W

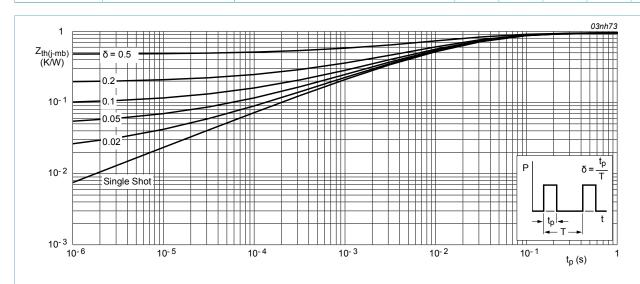


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
V _{(BR)DSS}	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	100	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 ^{\circ}\text{C}$	89	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 10	1	1.5	2	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 175 °C; Fig. 10	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	2.3	V
I _{DSS}	drain leakage current	V _{DS} = 100 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C	-	0.05	10	μA
I _{GSS}	gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon} drain-source on resistance	drain-source on-state	V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C	-	-	43	mΩ
	resistance	V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C; Fig. 11; Fig. 12	-	-	100	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	29	39	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; Fig. 11; Fig. 12	-	34	40	mΩ
Dynamic cl	haracteristics					
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 80 V; V _{GS} = 5 V;	-	48	-	nC
Q_{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13</u>	-	5.4	-	nC
Q_{GD}	gate-drain charge		-	20	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;	-	2304	3072	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 14</u>	-	222	266	pF
C _{rss}	reverse transfer capacitance		-	151	207	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 5 \text{ V};$	-	20	-	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega; T_j = 25 °C$	-	135	-	ns
t _{d(off)}	turn-off delay time		-	125	-	ns
t _f	fall time		-	90	-	ns
L _D	internal drain inductance	from upper edge of drain mounting base to centre of die; T _i = 25 °C	-	2.5	-	nH

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		from drain lead 6 mm from package to centre of die; T_j = 25 °C	-	4.5	-	nH
L _S	internal source inductance	from source lead to source bond pad; $T_j = 25 ^{\circ}\text{C}$	-	7.5	-	nH
Source-drain	diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 15$	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_S = 37 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	60	-	ns
Q _r	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	240	-	nC

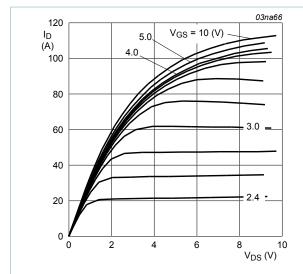
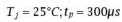


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values



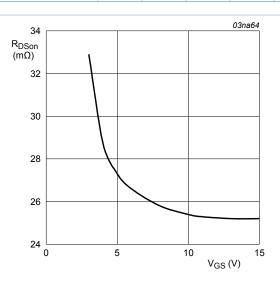


Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

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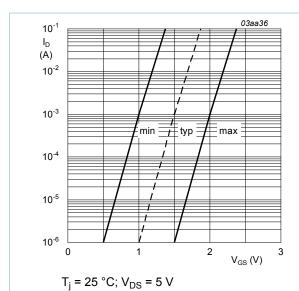
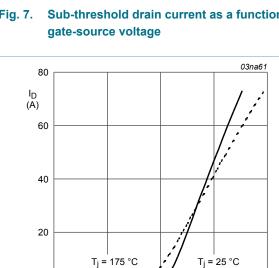


Fig. 7. Sub-threshold drain current as a function of



Transfer characteristics: drain current as a Fig. 9. function of gate-source voltage; typical values

3



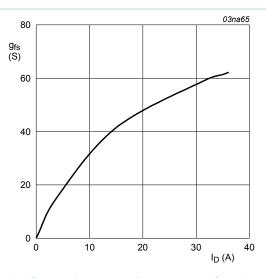


Fig. 8. Forward transconductance as a function of drain current; typical values

$$T_j=25^{\circ}C; V_{DS}=25V$$

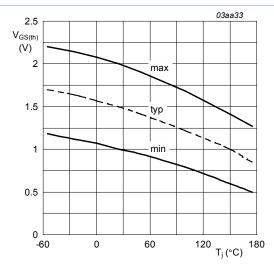


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 mA; V_{DS} = V_{GS}$$

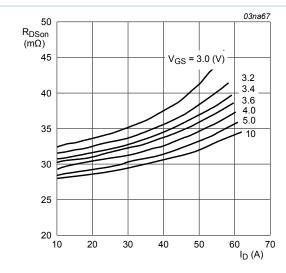


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25^{\circ}C$$

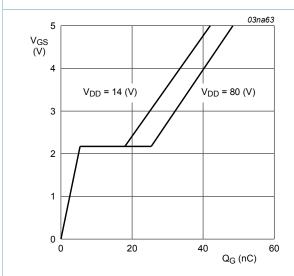


Fig. 13. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

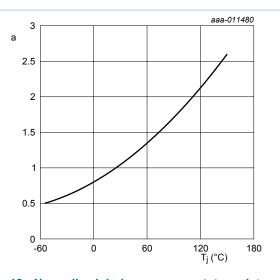


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

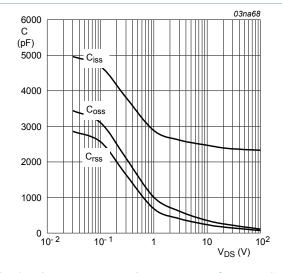


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$

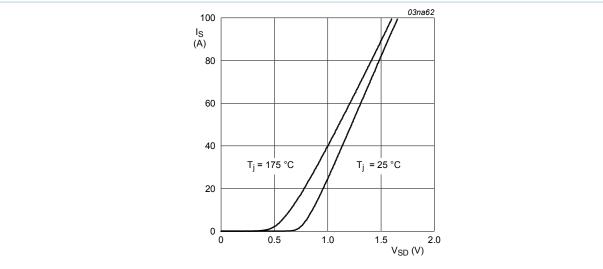
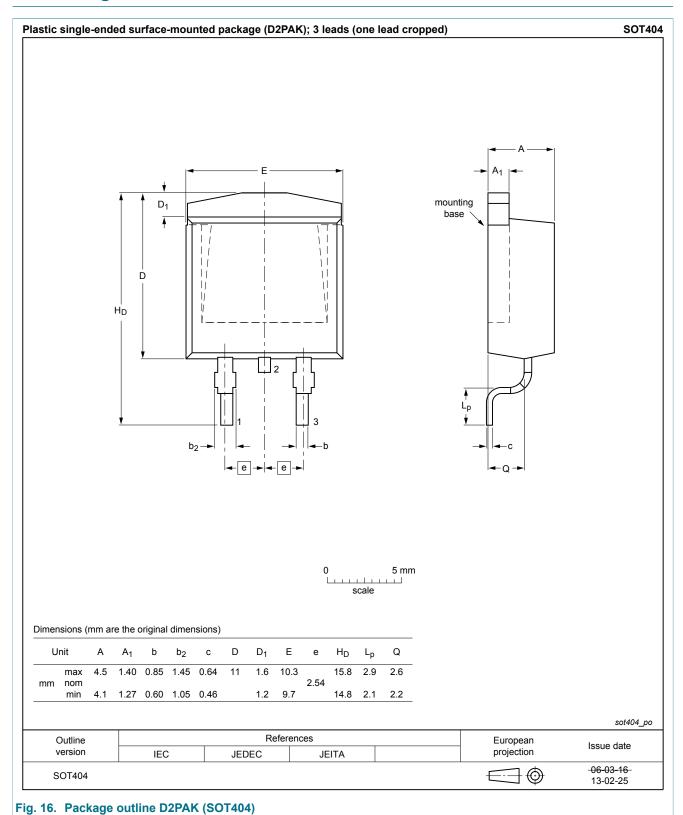


Fig. 15. Source current as a function of source-drain voltage; typical values

$$V_{GS} = 0V$$

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11. Package outline



BUK9640-100A

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12. Legal information

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